interface of said bottom surface and said sidewalls of said gate in a direction from said bottom surface toward and along said sidewalls;

(d) a unitary electrically conductive metallic material entirely covering said sidewalls and top surface of said gate; and

(e) source and drain regions in said semiconductor region defining a channel under said patterned gate.

Amend claim 9 as follows:

9. (Five Times Amended) A transistor gate structure, comprising:

(a) a gate dielectric over a semiconductor region;

(b) a patterned gate over said gate dielectric having sidewalls, a top surface and a bottom surface disposed on said gate dielectric;

(c) a lateral growth on said gate dielectric at the corners of said gate, but not under central regions of said gate, [increasing] the thickness of said gate dielectric continually increasing at the interface of said bottom surface and said sidewalls of said gate in a direction from said bottom surface toward and along said sidewalls; and

(d) a unitary electrically conductive metallic material entirely covering said sidewalls and top surface of said gate.